

25C D ■ 8235605 0004346 4 ■ SIEG

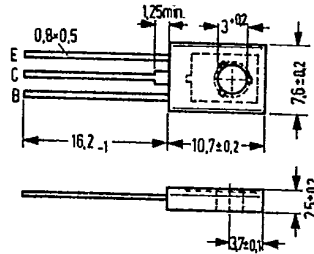
NPN Silicon Planar Transistor

BD 329

SIEMENS AKTIENGESELLSCHAFT 25C 04346 D T-33-07

BD 329 is an epitaxial NPN silicon planar transistor in TO 126 plastic package (12 A 3 DIN 41 869, sheet 4). Together with its complementary transistor BD 330 it is particularly suitable for use in complementary output stages of medium performance (e.g. car radios).

Type	Ordering code
BD 329	Q62702-D394
BD 329/BD 330 paired	Q62702-D401
Spring washer A 3 DIN 137	Q62902-B63



Approx. weight 0.5 g      Dimensions in mm  
 Transistor fixing with M3 screw  
 Starting torque max. 0.8 Nm  
 Washer or spring washer should be used.

**Maximum ratings**

Collector-emitter voltage	$V_{CES}$	32	V
Collector-emitter voltage	$V_{CEO}$	20	V
Emitter-base voltage	$V_{EBO}$	5	V
Collector current	$I_C$	3	A
Emitter current	$I_E$	3	A
Base current	$I_B$	1	A
Junction temperature	$T_j$	150	°C
Storage temperature range	$T_{stg}$	-55 to +150	°C
Total power dissipation ( $T_{amb} = 25^\circ\text{C}$ )	$P_{tot}$	15	W

**Thermal resistance**

Junction to ambient air	$R_{thJU}$	≤100	K/W
Junction to mounting area	$R_{thJC}$	≤7	K/W

392

1769

G-14

— SIEMENS AKTIENGESELLSCHAFT —

**Static characteristics ( $T_{amb} = 25^\circ\text{C}$ )**

Collector-emitter saturation voltage

( $I_C = 2\text{ A}; I_B = 200\text{ mA}$ )

Collector cutoff current

( $V_{CB} = 32\text{ V}$ )

Collector cutoff current

( $V_{CB} = 32\text{ V}; T_j = 150^\circ\text{C}$ )

Emitter cutoff current

( $V_{EB} = 5\text{ V}$ )

Base-emitter voltage

( $V_{CE} = 10\text{ V}; I_C = 5\text{ mA}$ )

( $V_{CE} = 1\text{ V}; I_C = 2\text{ A}$ )

DC current gain

$V_{CE} = 10\text{ V}; I_C = 5\text{ mA}$

$V_{CE} = 1\text{ V}; I_C = 0.5\text{ A}$

$V_{CE} = 1\text{ V}; I_C = 2\text{ A}$

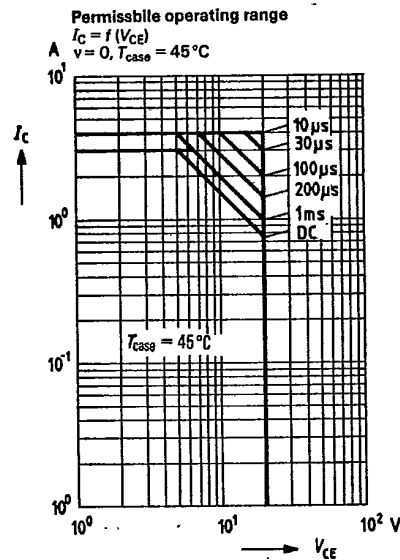
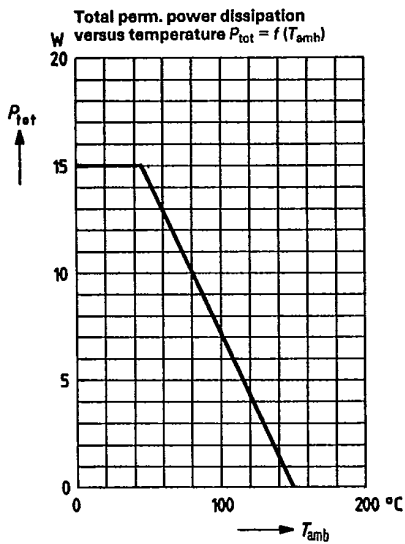
$V_{CEsat}$	$\leq 0.5$	V
$I_{CBO}$	$\leq 10$	$\mu\text{A}$
$I_{CBO}$	$\leq 1$	mA
$I_{EBO}$	$\leq 10$	$\mu\text{A}$
$V_{BE}$	0.6	V
$V_{BE}$	$\leq 1.2$	V
$h_{FE}$	$> 50$	—
$h_{FE}$	85 to 375	—
$h_{FE}$	$> 40$	—

**Dynamic characteristics ( $T_{amb} = 25^\circ\text{C}$ )**

Transition frequency

( $V_{CE} = 5\text{ V}; I_C = 50\text{ mA}$ )

$f_T$	130	MHz
-------	-----	-----



SIEMENS AKTIENGESELLSCHAFT

